Form PTO-1	449			ENT OF COMMERCE TRADEMARK OFFICE	ATTY, DOCKET MI22-2426	T NO.		SERIAL NO. 10/690,029				
OIP	8	IST OF ART CITED		π	APPLICANT: (Garo J. De	l	· 				
OEC 2	7 2004				FILING DATE October 20, 200	23						
U.S. PATER	ADE T DOC	UMENTS	-									
*Examiner's tritigis	_	Occurrent Number	Cate	Name		Crass	Supplass	Filing II App	Date ropriste			
W		6,753,618	06/2004	Basceri et al.		257	915					
	AS	5,470,794	11/1995	Anjum		437	200					
	AC	2003/0219942 A1	11/2003	Choi et al.		438	253	_				
	40	2004/0245560 A1	12/2004	Pontoh et al.		257	309					
	AE	2004/0245559 A1	12/2004	Pontoh et al.		257	306					
	AF	2004/0046197 A1	03/2004	Basceri et al.		257	296					
	40	2004/0043228 A1	03/2004	Derderian et al.		428	446		_			
V	A¥	2003/0213987 A1	11/2003	Basceri et al.	,	257	296	_				
w	*	2003/0205729 A1	11/2003	Basceri et al.		257	200					
FOREIGN F	ATEN	DOCUMENTS	1				· · · · · · · · · · · · · · · · · · ·					
,		Document Number	Date	Country		Class	Subclasts	Yes.	tation No			
	N											
	AK			·								
	AL											
OTHER RE	FEREN	ICES (including Author	, Title, Oate, Po	ertinent Pages, Elc.)								
	ли											
	**											
	8				1							
							·					
EXAMINER A.)	11.0	DATE CONSID		luns								
V				on is in conformance with MF	PEP 609: Draw line !	hrough cita	tion it not in c	onioman~	and not			
		copy of this form with next										

Form PTO	E		PATENT AND	IENT OF COMMERCE TRADEMARK OFFICE IT	ATTY. DOCKET MI22-2428 APPLICANT: 1		10/69	90,029	
Shierran	MODELL S				FILING DATE October 20, 200	03	1	••	
U.S. PATEN	IT DOO	UMENTS					<u></u>	-	
"Examiner's Initiate		Document Number	Date	Nzme		Class	Subclass		
hu	4	3,349,474	12/1963	D. H. Rauscher		•		-	_
	AB	5,904,517	05/1999	Gardner et al.		438	197	-	
	*	5,998,264	12/1999	Wu		10/690,029		$\overline{}$	
	2	6,180,465 B1	01/2001	Gardner et al.		10/690,029 AT: Garo J. Derderian et al. ATE D, 2003 GROUP 2812 Class Subclass Filing Date If Appropriate A38 197 438 260 438 291 438 216 257 310 Class Subclass Translation Yes No X Class Subclass Translation Yes No X		<u></u>	
1/	Æ	6,207,485 B1	03/2001	Gardner et al.		438	216		 ,
hn	M	6,548,854 B1	04/2003	Kizilyalli et al.		257 -	310	_	
	AG.								
h	¥	2003/0045060 A1	03/2003	Ahn et al.		·438	287		
m	A	2003/0045078 A1	03/2003	Ahn et al.		438	585		
FOREIGN P	ATENT	DOCUMENTS					· · · · · · · · · · · · · · · · · · ·		
		Document Number	Date	Country		Class	Subclass		
W	~	EP 0 851 473 A2	01/1998	EPO		_			
	AK								
	AL								
OTHER RE	FEREN	CES (including Author,	Title, Date, Pe	erlinent Pages, Etc.)					
a		Chang et al., S. (2004), pages		reatments in advanced i	NOS gate process	ing, Micn	oelectronic E	nglneerin	9.
V									
les	4	Lemberger et a novel MOCVD	II., Electrical ch precursors, Mi	naracterization and reliab croelectronic Engineerin	ility aspects of zing (2004), pages 3	oonium si 15-320	licate films o	blained fr	om
. ,	AG.	Lu et al., Effect	s of the TaN, i	nterface layer on doped t	antalum oxide hig	h-k films	VACUUM (2004), pag	ges 1-9.
m					· · ·				
EXAMINER VILLE	H.a	DATE CONSIDER	RED 47	luns					
		7 reference considered, what opy of this form with next or			EP 609; Drawline U	wough cita	ation if not in or	onformance	ton bns

	Form PTO-1449
/ 0'	C 48
/ ₅₀₀ /	2 2004
250	
AL TERE	BY CE
AM	5118

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)

ATTY. DOCKET NO. Mi22-2428 SERIAL NO. 10/690,029

APPLICANT: Garo J. Derderian

FILING DATE October 20, 2003

GROUP 2812

MARK											
U.S. PATE	NT DOC	CUMENTS	<u> </u>								
Examiners Initials		Document Number	Date	Mamo		٥	353	Subs	dass		optate g Date
w	*	4,086,074	04/78	Minot et al.							
	AÐ	4,622,735	11/86	Shibata							
	AC	4,683,645	08/87	Naguib et al.							 ,
	AO	4,693,910	09/87	Nakajima et al.							
	Æ	4,766,090	08/88	Coquin et al.							
	45	5,099,304	03/92	Takemura et al.						_	
1/	Α0	5,236,865	08/93	Sandhu et al.						_	
V,	AH	5,444,024	08/95	Anjum et al.						_	
h	AJ	5,470,784	11/95	Anjum et al.						_	
FOREIGN	PATEN	F DOCUMENTS									
		Document Number	Date	Country		Q	855	Şubci	855	Trans	dadon
	-								\dashv	Yes	No
									\dashv		-
	AK					_			\dashv		
OTHER R	EFEREN	ICES (including Au	thor, Title, Date, P	erlinent Pages, Etc.)							
• /	M	ABSTRAC 2004		Atomic Layer Deposition f	or Nanoscale CU	Me	aliza	tlen, 10) page	es (pre-Ap	oril
4											
• /	м			ion implantation reactor of NOLOGY 64-69 (1966).	lesign consideration	ons	for o	dde ch	arging	g. 85 SUR	FACE
w										1-1	
1	م	Ku et al., 1 Silicit	The Application of the Technology, 13	lon Beam Mixing, Doped : 7 J. Electrochem. Soc. No.	Silicide, and Rapid 2. 2, pp. 728-740 (d Th	ema	l Proc 1990)	essing -	of Self-A	ligned
m					•						
EXAMINER		DATE CON	SIDERED	- /							
Via	Hom	9/		3/2005							
	t; Initial if	-y		ion is in conformance with MP	PEP 609; Draw line th	hrou	gh cit	ation if n	iol In c	onformance	e and not

Prop PTO-1	1449	U F	ATTY. DOCKE MI22-2426	SERIAL NO. 10/690,029									
ions of		UST OF ART CITED (Use several shapes		APPLICANT:			J. Derds	rian	•				
MAGES OF THE PATEN					FILING DATE October 20, 20	03		GROUP . 2812					
U.S. PATEN	T DOC	UMENTS	<u>.</u>	·									
Examiner's Inhiels		Document Number	Cate	Name		Clas	is 5	obclass	s Filing Date If Appropriate				
m	*	2001/0006759 A1	07/01	Shipley, Jr. et al.			`	1		_			
	48	2002/0076879 A1	06/02	Lee et al.									
1	æ	2002/0196651 A1	12/02	Weis					_				
W	8	2003/0013272 A1	01/03	Hong et al.				1					
	Æ								<u> </u>	_			
	A\$												
	¥9												
	a)												
	2												
FOREIGN F	ATENT	DOCUMENTS				т-							
•		Document Number	Date	Country	,	Cla	53 S	dictass	Tran: Yes	dation No			
	نه												
	AK												
	AL.												
OTHER RE	FEREN	CES (including Author	, Title, Oate, P	ertinent Pages, Etc.)									
	"		-										
	м.				,								
ļ			~										
	40												
		, DATE CONSIDE	EREO					-					

Pro Pro	1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			T NO.	SERIAL NO. 10/690,029			
027004		LIST OF ART CITED (Use several sheats		NT .	APPLICANT: Garo J. Derderlan					
BADEMARK	<i>,</i>			·	FILING DATE October 20, 20	03		GRC 2812		
U.S. PATEN	T DOC	UMENTS			•					
"Examiner's tritists		Document Number	Oate	Name		Class	Subclass		Arbeitass Filing Date If Appropriate 06/03	
m		10/609,311		Yates						
	A 5	10/655,997		Daley					09/03	
	AC,	10/689,958		Basceri				T	10/03	
\mathbb{V}	AĐ	10/882,118		Sandhu et al.			Γ		04/04	
hw	AE	10/879,367		Blafock et al.			1	1	06/04	
	45						T			
	*0									
	AH						1			
	Al						T			
FOREIGN P	ATENT	DOCUMENTS	d						•	-
•		Document Number	Оже	Country		Class	Sa.	Delga3	Trans Yes	station No
	W								1,00	
	AK						1			
	AL						T			
OTHER RE	FEREN	CES (including Author,	, Title, Date, P	ertinent Pages, Etc.)		<u> </u>				
	A44		·····							
	Ī									
	~									
	ľ									
	40									
									<u>,</u> ,	
EXAMINER 1	Hom	DATE CONSIDE	RED al	2005						

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF ART CITED BY APPLICANT			ATTY. DOCKE MI22-2426	T NO.		SERIAL NO. 10/690,029			
NOTE OF STREET		(Use several sheats	K nacessary)		APPLICANT:	n					
MARKO	•					03		GROUP 2812			
U.S. PATER	VT DOC	UMENTS		•				·			
"Examiner's Initials		Document Number	Oate	Name		Class	Subct		ing Date opropriate		
W	^	5,670,298	09/97	Hur							
1	A6	6,037,239	03/00	Jennings							
	Æ	6,096,621	08/00	Jennings							
	40	6,130,140	10/00	Gonzalez							
	42	6,133,105	10/00	Chen et al.	•						
	AF	6,133,116	10/00	Kim et al.				_			
1	~	6,177,235 81	01/01	Francou et al.		IT		-			
1/	AH	6,277,709 B1	08/01	Wang et al.				_			
m	~	6,277,728 81	08/01	Ahn et al.							
FOREIGN	PATENT	DOCUMENTS									
		Document Number	Date	Country	· 	Class	Subda	ts Tre	nstation		
	A										
	AK .										
	44										
OTHER RE	FEREN	CES (including Author,	, Title, Date, P	ertinent Pages, Etc.)							
h	м	ABSTRACT: Het al.; 4 pages		te Voiding in Paraus-Low	-k Dielectrics and	The Med	hanism	of Void Form	ation; l		
W	м	COB Stack OF 349.3;	RAM Cell Tech	nology beyond 100 nm T	echnology Node;	Yongjik P	ark & K	inam Kim; pp	, 349.1		
w	40			n Dioda Formation by Im 7 IEEE Transactions on E							
EXAMINER	Ha	DATE CONSIDE	ERED	3/205	•			, — , — , — , — , — , — , — , — , — , —			

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF ART CITED BY APPLICANT			ATTY. DOCKE MI22-2426	T NO	SERIAL NO. 10/690,029					
2004		(Use several shoe		"	APPLICANT:	Gard) J.	Derd	erian		<u>.</u>	
MARK W			•			03				GROUP 2812		
U.S. PATE	NT DOC	UMENTS		•	,							
Examiner's britishs	,	Document Number	Date	Name		a	253	T.	Subclass	Filin II Ap;	ng Date propriete	
h	4	6,440,793 B1	08/02	Divakaruni et al.			L			T		
	9	6,465,325 B2	10/02	Ridley et al.						T		
.]	AC	6,720,638 B2	04/04	Tran					7_	T		
	40	6,780,728 B2	08/04	Tran				$T_{}$		T_		
	AE 6,156,674 12/00 Li et al.					$T_{}$		 -	_			
	AF	6,281,100 B1	08/01	Yin et al.						T_ <u>-</u>		
	AG	6,291,363 B1	09/01	Yin et al.							<u> </u>	
V	AH	6,380,611 B1	04/02	Yin et al.				I		_	_	
le	AJ	6,383,723 81	05/02	iyer et al.			_	Ŧ	上	_		
FOREIGN	PATENT	F DOCUMENTS				_		_				
	,	Occument Number	Date	Country		a	asa	S	ubclass	Yes	station No	
	W					<u> </u>		1				
	AX											
	. AL							\top				
OTHER R	EFEREN	ICES (including Autho	ar, Title, Date, P	ertinent Pages, Etc.)	,	<u> </u>	-			<u> </u>		
	м.											
								·	<u></u>			
	-				<u> </u>		_					
	~											
EXAMINER	Ha	DATE CONSID		3/2015							•	